

Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No.	NOVLP091/NVLS-2889
	Application No.:	10/820,525
	Applicants	WU, Qingguo, et al.
	Filing Date	April 7, 2004
	Group	2823
	Conf. No.	8337
	Submitted on:	November 9, 2009

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-cla	Filing Date
	1.	7,390,537	06.24.08	Wu et al.			
	2.	7,381,659 B2	06.2008	Nguyen et al.			
	3.	2008/0009141 A1	01.2008	Dubois et al.			
	4.	2008/0132055 A1	06.2008	Nguyen et al.			
	5.	7,341,761	03.11.08	Wu et al.			
	6.	7,381,662	06.03.08	Niu et al.			
	7.	6,5702,56	05.2003	Conti et al.			
	8.	2005/0260357	11.2005	Zheng et al.			
	9.	2008/0194105	08.2008	Dominquez et al.			
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	13.	2006/0145304	7.2006	Boyanov et al.			
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	18.	6,890,850	5.2005	Lee et al.			
	19.	2004/0166240 A1	08.2004	Rhee et al.			
	20.	2005/0025892 A1	02.2005	Satoh et al.			
	21.	2006/0024976 A1	02.2006	Waldfried et al.			
	22.	6,436,824	08.2002	Chooi et al.			
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Foreign Patent or Published Foreign Patent Application

Examiner Initial	Document No.	Publication Date	Country or Patent Office	Class	Sub-Class	<u>Translation</u>	
						Yes	No

Examiner /Julio Maldonado/	Date Considered 04/07/2010
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	24.						
	25.						

Other Documents

Examiner Initial	No.	Author, Title, Place (e.g. Journal) of Publication, Date
	26.	U.S. Office Action mailed March 31, 2008, from U.S Application No. 10/820,525 [Att Dkt No. NOVLP091/NVLS-2889].
	27.	U.S. Office Action dated July 10, 2008, from U.S. Application No. 10/807,680 [Atty Dkt: NOVLP97/NVLS-2906]
	28.	U.S. Office Action mailed August 5, 2008, from U.S Application No. 10/987,208 [Atty Dkt No. NOVLP104/NVLS-2928].
	29.	U.S. Final Office Action mailed May 29, 2008, from U.S Application No. 11/764,750 [Atty Dkt No. NOVLP106D1/NVLS-2930D1].
	30.	U.S. Notice of Allowance and Fee Due mailed August 25, 2008, from U.S. Application No. 11/764,750. [NOVLP106D1/NVLS-2930D1]
	31.	Allowed Claims from U.S. Application No. 11/764,750. [NOVLP106D1/NVLS-2930D1]
	32.	Solomons and Fryhle, Organic Chemistry, 9 th Edition, John Wiley & Sons, Inc., 2008, pages 602-603
	33.	Wu et al., Methods for Fabricating High Hardness/Modulus Low Dielectric Constant Materials," Novellus Systems, Inc., App. No. 11/369,658, filed March 6, 2006. [NOVLP148/NVLS-3111]
	34.	Szekeres, A et al., "Plasma-assisted chemical vapor depositing silicon oxynitride as an alternative material for gate dielectric in MOS devices." Microelectronics Journal 37 (2006) pp. 64-70.
	35.	U.S. Office Action for Application No. 11/369,658 mailed 12/12/2008 [Attorney Docket No. NOVLP148]
	36.	U.S. Office Action for Application No. 10/987,208 mailed 2/4/2009 [Attorney Docket No. NOVLP104]
	37.	U.S. Office Action for Application No. 11/606,340 mailed 2/5/2009 [Attorney Docket No. NOVLP100C1]
	38.	U.S. Office Action for Application No. 11/936,754 mailed 6/19/2009 [Attorney Docket No.: NOVLP098D1]
	39.	U.S. Final Office Action for Application No. 10/987,208 mailed 7/10/2009 [Attorney Docket No. NOVLP104]
	40.	U.S. Office Action for Application No. 11/369,658 mailed 7/8/09 [Attorney Docket No. NOVLP148]
	41.	Wu et al., PECVD Methods For Producing Ultra Low-K Dielectric Films Using UV Treatment," Novellus Systems, Inc., App. No. 11/608,056, filed December 7, 2006. [NOVLP196/NVLS-3238]

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	42.	U.S. Office Action for Application No. 11/608,056 mailed 8/20/09 [Attorney Docket No. NOVLP196/NVLS-3238]
	43.	Wu et al., Methods For Improving Performance of ODC Films With Dielectric Constant < 4.0," Novellus Systems, Inc., App. No. 11/693,661, filed March 29, 2007. [NOVLP200/NVLS-3269]
	44.	U.S. Office Action for Application No. 11/693,661 mailed August 28, 2009 [Attorney Docket No. NOVLP200]
	45.	Wu et al., "Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups", U.S. Application No. 12/348,791, filed January 5, 2009 [Atty Dkt: NOVLP106D1C1/NVLS-2930D2]
	46.	Wu et al., "Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups", U.S. Application No. 12/479,114, filed June 5, 2009 [Atty Dkt: NOVLP106D1C2/ NVLS-2930D1C2]
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